

TI PRIME

adhesion promoter

Technical Data Sheet
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General Information

The TI PRIME adhesion promoter improves resist adhesion on substrates like Si or glass

Processing the TI PRIME

(in chronological order)

- **Substrate preparation:** After (optional, but recommended) cleaning the substrate with acetone and subsequently isopropyle, put the substrate on the hotplate at a minimum temperature of 120 °C for 10 minutes to remove adsorbed water from the substrates surface. Alternatively, you can use a furnace at same temperature for 30 min.
- **Spin coat the TI PRIME** at approx. 2000-4000 U/min for approx. 20 seconds. After spin-coating, no residual drops or film of TI PRIME should be visible.
- **Bake** the substrate at 120°C for 2 minutes on the hotplate (when using a furnace, 130°C for 10 min is recommended)
- **Proceed** with spin-coating the resist immediately and proceed as usual.

Note: TI Prime contains Titanium. For CMOS processes use (eg. RCA-) cleaning procedure of the substrates after lithography before you apply high-temperatures.

